

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph beginning at page 12, line 18 with the following amended paragraph:

A preferred embodiment showing a manner in which shock absorbers 528, 530 are employed in an ESD device 500 is shown in Fig. 5. It should be noted that the preferred embodiments disclosed herein could be employed in various combinations. The specific structure corresponds to a MOSFET switch such as switch 416 shown in Fig. 4. However, the modifications can equally be applied to any other switch type, such as bipolar transistor, SCR or other known ESD switch type. By way of example, the active device region of an ESD switch comprises a source 512 and a drain 516 region connected by a channel 514 region, formed in substrate 510. The switch also has a gate 524 and dielectric 526. Connecting the active device regions are source 522, gate contact 520 and drain 518 connectors.

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